



20V P-CHANNEL ENHANCEMENT MODE MOSFET POWERDI[®]

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
	$5.5 m\Omega$ @ $V_{GS} = -10V$	-40A
-20V	$7.0 \text{m}\Omega$ @ $V_{GS} = -4.5 \text{V}$	-40A
	$9.0 \text{m}\Omega$ @ $V_{GS} = -2.5V$	-40A

Features

- Low R_{DS(ON)} ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description

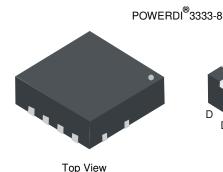
This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high- efficiency power management applications.

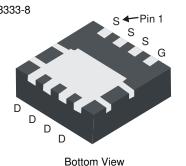
Applications

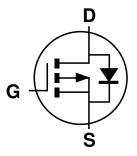
- Load Switch
- Power Management Functions

Mechanical Data

- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.030 grams (Approximate)







Equivalent Circuit

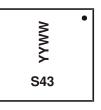
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2007UFG-7	POWERDI3333-8	2,000/Tape & Reel
DMP2007UFG-13	POWERDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



S43 = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 14 = 2014) WW = Week Code (01 ~ 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	-20	V		
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5) $V_{GS} = -10V$ Steady State		I _D	-18.0 -14.5 -40	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-80	Α		
Maximum Continuous Body Diode Forward Current (Note 5)			Is	-2.2	Α
Avalanche Current L=0.1mH			las	-30	Α
Avalanche Energy L=0.1mH			E _{AS}	50	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	D	2.3	W
Total Fower Dissipation (Note 5)	$T_{C} = +25^{\circ}C$	P_{D}	41	
Thermal Resistance, Junction to Ambient	(Note 5)	D	58	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	143	
Thermal Resistance, Junction to Case	$R_{ heta JC}$	3.0		
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV_DSS	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -16V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-0.4		-1.3	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
		1	4.4	5.5		$V_{GS} = -10V, I_D = -15A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	4.9	7.0	mΩ	$V_{GS} = -4.5V, I_D = -15A$	
		l	6.5	9.0		$V_{GS} = -2.5V, I_D = -10A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -10A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		4,621	_		V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss		652	_	рF		
Reverse Transfer Capacitance	Crss		403	_			
Gate Resistance	Rg		3.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	1	39	_	nC Vpp = -10V lp = -20A		
Total Gate Charge (V _{GS} = -10V)	Q_g		85	_			
Gate-Source Charge	Q_{gs}	_	8.3	_	IIC	$V_{DD} = -10V, I_D = -20A$	
Gate-Drain Charge	Q_{gd}	_	9.6	_			
Turn-On Delay Time	t _{D(ON)}	_	10.1	_			
Turn-On Rise Time	t _R	_	9.8	_		$V_{GS} = -4.5V, V_{DD} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	61	_	ns	$R_G = 1\Omega$, $I_D = -10A$	
Turn-Off Fall Time	t _F	_	51	_			
Reverse Recovery Time	t _{RR}		20.1	_	ns	I _F = -10A, di/dt = 100A/μs	
Reverse Recovery Charge	Q _{rr}	_	10.1	_	nC	$I_F = -10A$, $di/dt = 100A/\mu s$	

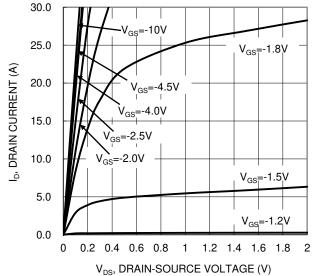
Notes: 5. R_{8JA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R_{8JC} is guaranteed by design while R_{8JA} is determined by the user's board design.

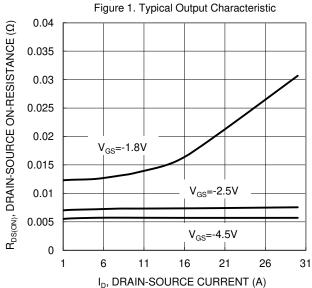
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

 $^{7. \} Short \ duration \ pulse \ test \ used \ to \ minimize \ self-heating \ effect.$

^{8.} Guaranteed by design. Not subject to product testing.







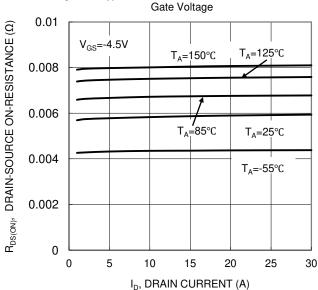
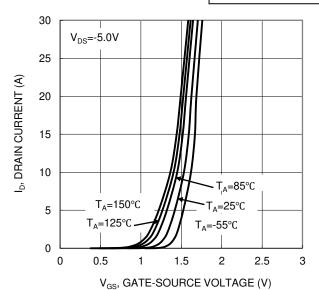


Figure 3. Typical On-Resistance vs Drain Current and

Figure 5. Typical On-Resistance vs Drain Current and Temperature



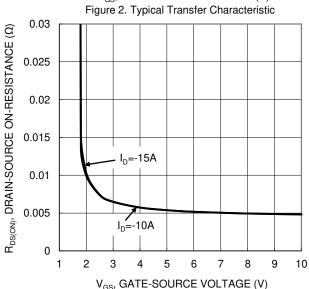


Figure 4. Typical Transfer Characteristic

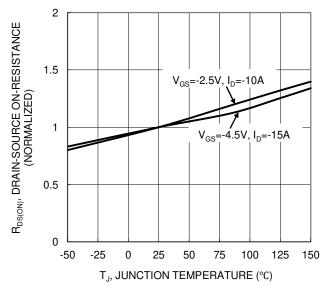
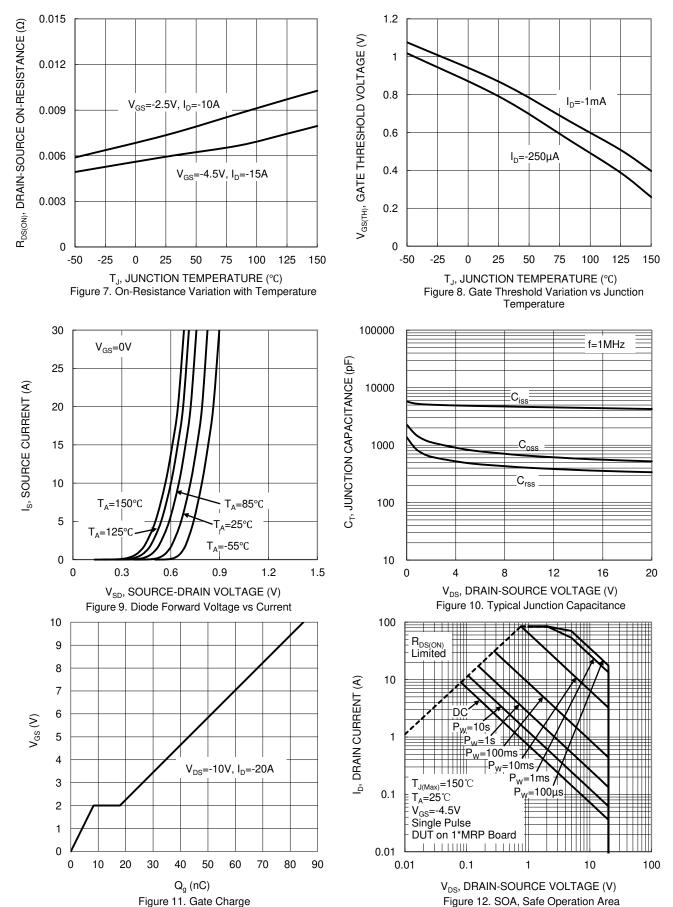
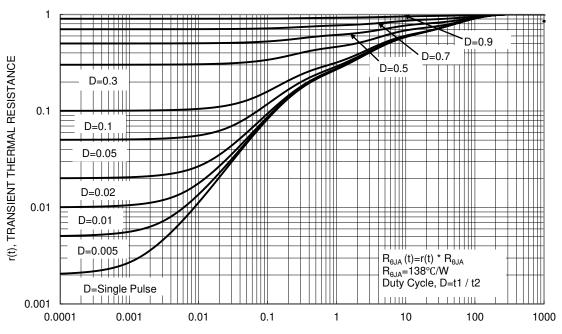


Figure 6. On-Resistance Variation with Temperature







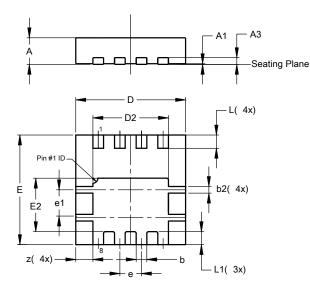


t1, PULSE DURATION TIME (sec)
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

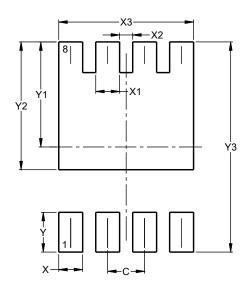
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI®3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A 1	0.00	0.05	0.02		
A3	_	_	0.203		
b	0.27	0.37	0.32		
b2	_	_	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
е	_	_	0.65		
e1	0.79	0.89	0.84		
L	0.35	0.45	0.40		
1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		



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